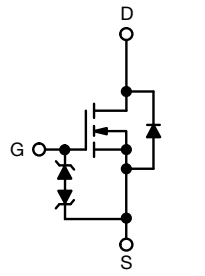
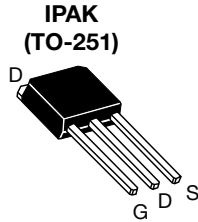


## E Series Power MOSFET



N-Channel MOSFET

### FEATURES

- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low effective capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)
- Integrated Zener diode ESD protection
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Renewable energy

### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	850	
$R_{DS(on)}$ typ. ( $\Omega$ ) at 25 °C	$V_{GS} = 10$ V	1.17
$Q_g$ max. (nC)	16.5	
$Q_{gs}$ (nC)	3	
$Q_{gd}$ (nC)	6	
Configuration	Single	

### ORDERING INFORMATION

Package	IPAK (TO-251)
Lead (Pb)-free and halogen-free	SiHU5N80AE-GE3


### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	800	V
Gate-source voltage	$V_{GS}$	$\pm 30$	
Continuous drain current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current <sup>a</sup>	$I_{DM}$	7	
Linear derating factor		0.5	W/°C
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	17	mJ
Maximum power dissipation	$P_D$	62.5	W
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Drain-source voltage slope	$dv/dt$	$T_J = 125$ °C	V/ns
Reverse diode $dv/dt$ <sup>d</sup>		0.3	
Soldering recommendations (peak temperature) <sup>c</sup>	For 10 s	260	°C

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 1.1$  A
- 1.6 mm from case
- $I_{SD} \leq I_D$ ,  $di/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C

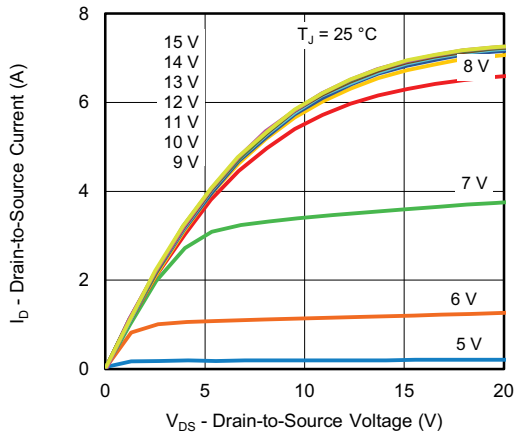
<b>THERMAL RESISTANCE RATINGS</b>			
PARAMETER	SYMBOL	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	62	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	2	

<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	800	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$	-	0.8	-	V/°C
Gate-source threshold voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	-	4	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 10$	$\mu\text{A}$
		$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 50$	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 640\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 1.5\text{ A}$	-	1.17	1.35	$\Omega$
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 2\text{ A}$	-	1.2	-	S
<b>Dynamic</b>						
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	321	-	pF
Output capacitance	$C_{oss}$		-	20	-	
Reverse transfer capacitance	$C_{rss}$		-	4	-	
Effective output capacitance, energy related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$	-	14	-	pF
Effective output capacitance, time related <sup>b</sup>	$C_{o(tr)}$		-	71	-	
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}, I_D = 2\text{ A}, V_{DS} = 640\text{ V}$	-	11	16.5	nC
Gate-source charge	$Q_{gs}$		-	3	-	
Gate-drain charge	$Q_{gd}$		-	6	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 640\text{ V}, I_D = 2\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$	-	12	24	ns
Rise time	$t_r$		-	8	16	
Turn-off delay time	$t_{d(off)}$		-	10	20	
Fall time	$t_f$		-	28	56	
Gate input resistance	$R_g$		$f = 1\text{ MHz}, \text{open drain}$	1.6	3.2	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	4.4	A
Pulsed diode forward current	$I_{SM}$		-	-	7	
Diode forward voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 2\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$	-	267	534	ns
Reverse recovery charge	$Q_{rr}$		-	1.2	2.4	$\mu\text{C}$
Reverse recovery current	$I_{RRM}$		-	7.5	-	A

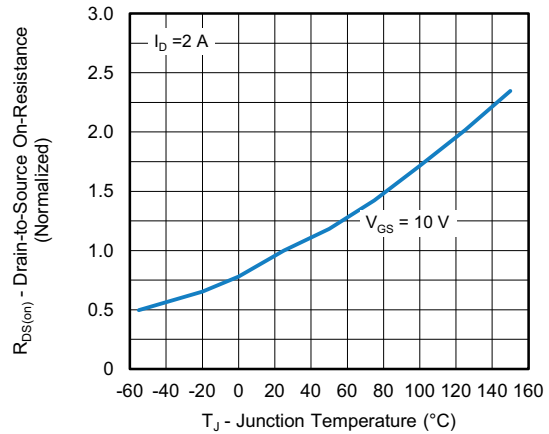
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 V to 480 V  $V_{DSS}$   
 b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 V to 480 V  $V_{DSS}$

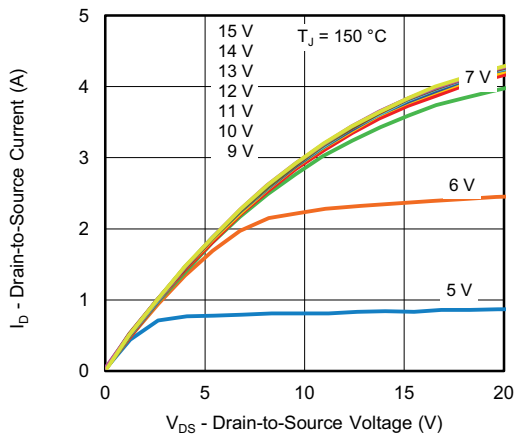
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



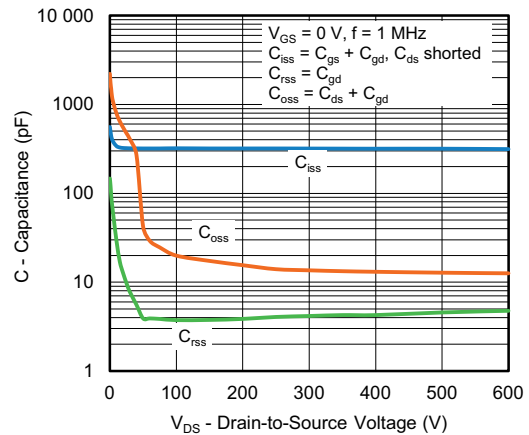
**Fig. 1 - Typical Output Characteristics**



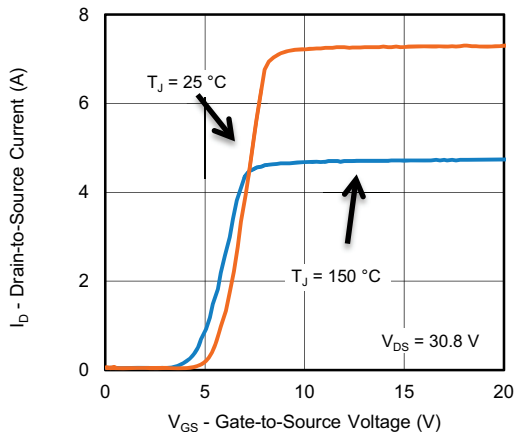
**Fig. 4 - Normalized On-Resistance vs. Temperature**



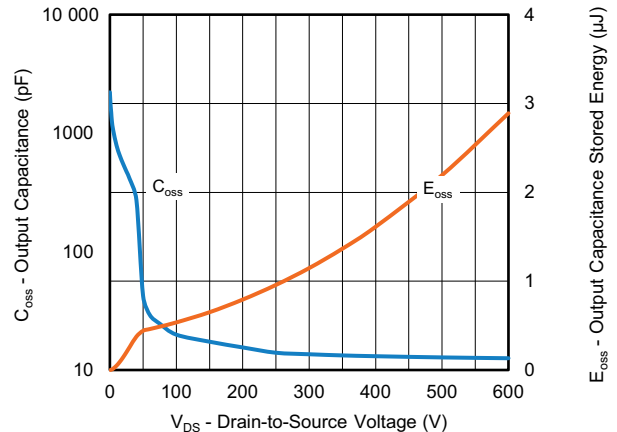
**Fig. 2 - Typical Output Characteristics**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$**

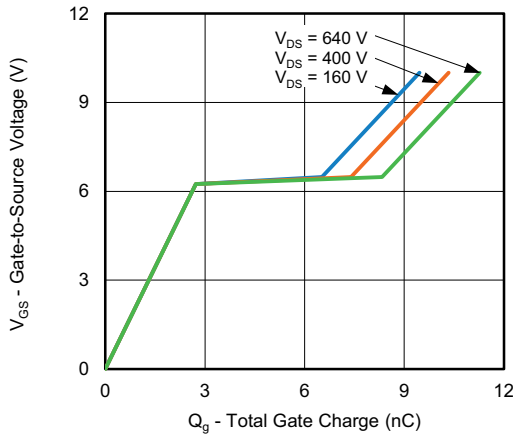


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

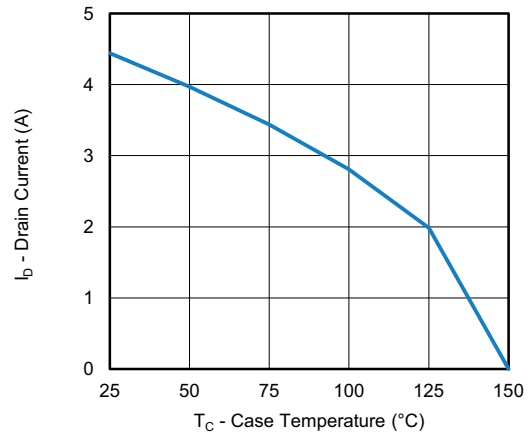


Fig. 10 - Maximum Drain Current vs. Case Temperature

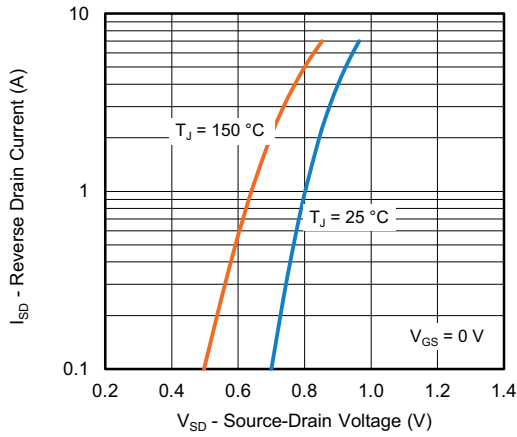


Fig. 8 - Typical Source-Drain Diode Forward Voltage

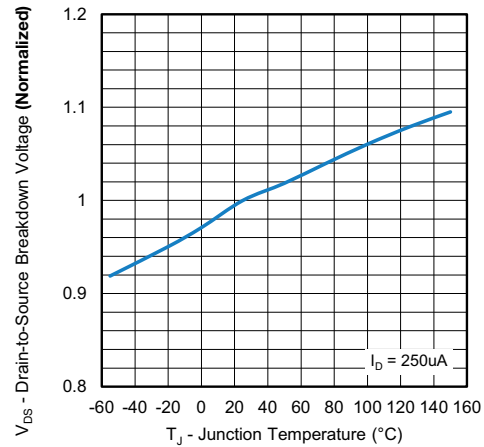


Fig. 11 - Normalized Breakdown Voltage vs. Temperature

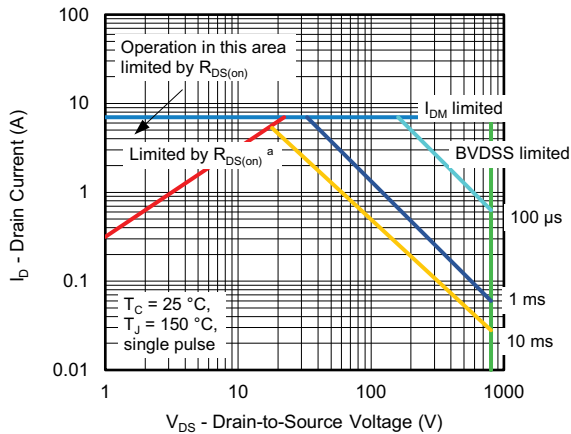


Fig. 9 - Maximum Safe Operating Area

**Note**

a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

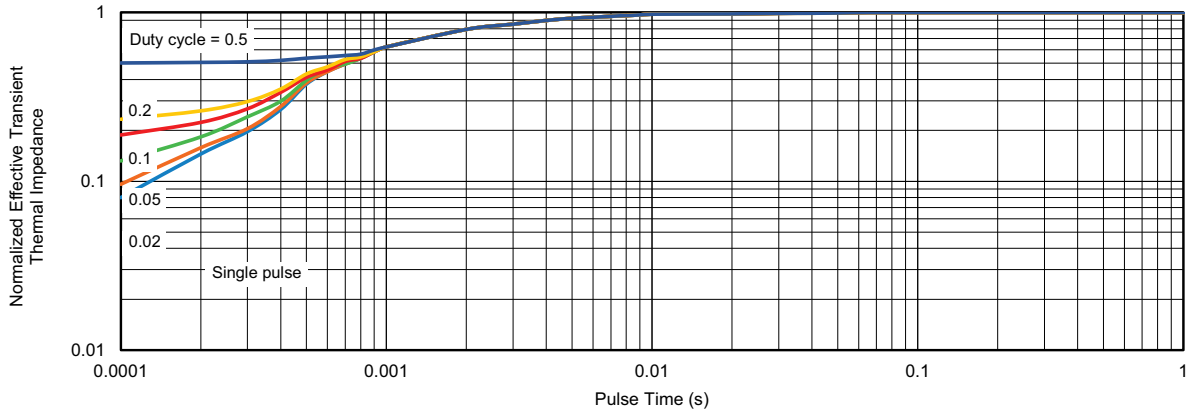


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case



Fig. 13 - Switching Time Test Circuit



Fig. 16 - Unclamped Inductive Waveforms

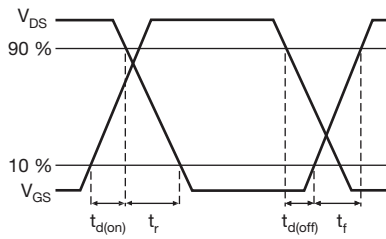


Fig. 14 - Switching Time Waveforms



Fig. 17 - Basic Gate Charge Waveform



Fig. 15 - Unclamped Inductive Test Circuit

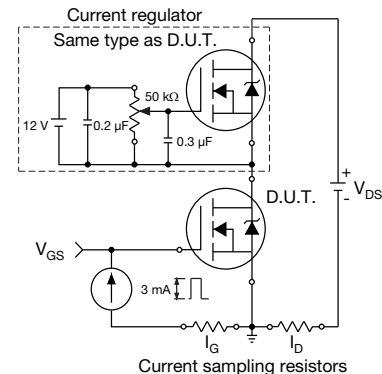


Fig. 18 - Gate Charge Test Circuit



**Note**  
a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 19 - For N-Channel**

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